BUJD103AD

NPN power transistor with integrated diode

Rev. 3 — 3 August 2010

Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT428 (DPAK) surface-mountable plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability

- Integrated anti-parallel E-C diode
- Very low switching and conduction losses

1.3 Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _C	collector current	see Figure 1; see Figure 2; DC; see Figure 4	-	-	4	Α
P _{tot}	total power dissipation	see <u>Figure 3</u> ; T _{mb} ≤ 25 °C	-	-	80	W
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	700	V
Static chara	acteristics					
h _{FE}	DC current gain	$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V};$ see <u>Figure 10</u> ; $T_j = 25 ^{\circ}\text{C}$	13	21	32	
		$V_{CE} = 5 \text{ V}; I_C = 3 \text{ A};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{ or } 10}$	-	12.5	-	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector[1]	mb	c L
3	Е	emitter	1 3	B
			SOT428 (DPAK)	

^[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJD103AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	DC; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 4</u>	-	4	Α
I _{CM}	peak collector current	see Figure 1; see Figure 2; see Figure 4	-	8	Α
I _B	base current	DC	-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see <u>Figure 3</u>	-	80	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C

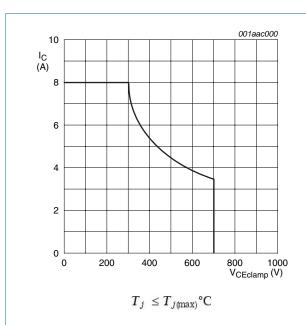
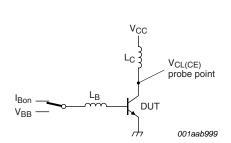


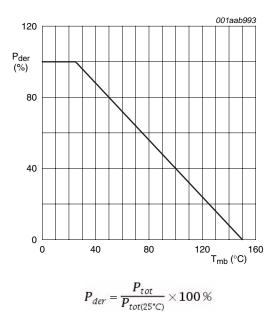
Fig 1. Reverse bias safe operating area



$$V_{CL(CE)} \le 1000 \; V; V_{CC} = 150 \; V; V_{BB} = -5 \; V;$$

$$L_B = 1 \; \mu H; L_C = 200 \; \mu H$$

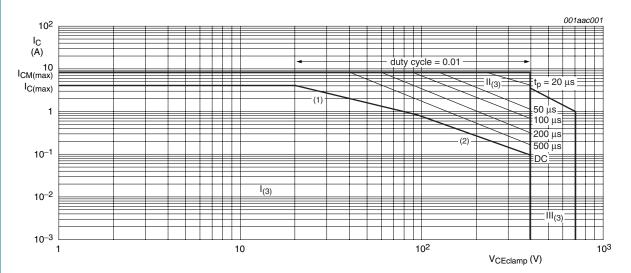
Fig 2. Test circuit for reverse bias safe operating area



Normalized total power dissipation as a function of mounting base temperature

 $P_{der} = \frac{1}{P_{tot(25^{\circ}C)}} \times 100$

Fig 3.



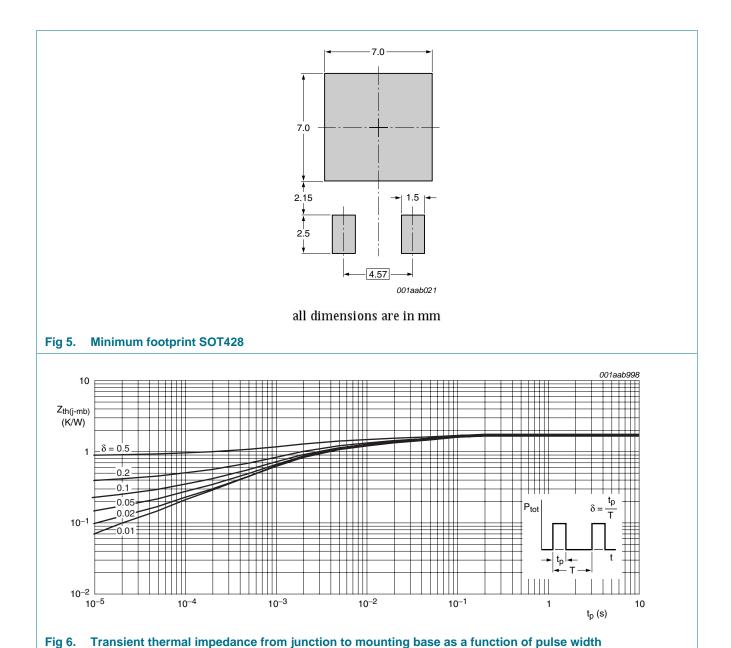
- 1) Ptot maximum and Ptot peak maximum lines
- 2) Second breakdown limits
- 3) I = Region of permissable DC operation
 - II = Extension for repetitive pulse operation
 - III = Extension during turn-on in single transistor converters provided that $R_{BE} \leq 100~\Omega$ and $t_p \leq 0.6~\mu s$

Fig 4. Forward bias safe operating area for T_{mb} ≤ 25 °C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 6	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed-circuit-board mounted; minimum footprint; see Figure 5	-	75	-	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
I _{CES}		$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	<u>[1]</u>	-	-	2	mΑ
	current	V_{BE} = 0 V; V_{CE} = 700 V; T_j = 25 °C	<u>[1]</u>	-	-	1	mΑ
I _{CBO}	collector-base cut-off current	$V_{CB} = 700 \text{ V}; I_E = 0 \text{ A}$	<u>[1]</u>	-	-	1	mA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}$	<u>[1]</u>	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V; } I_{C} = 0 \text{ A}$		-	-	10	mA
V_{CEsat}	collector-emitter saturation voltage	$I_C = 3 \text{ A}$; $I_B = 0.6 \text{ A}$; see <u>Figure 7</u> ; see <u>Figure 8</u>		-	0.29	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3 \text{ A}$; $I_B = 0.6 \text{ A}$; see Figure 9		-	0.99	1.5	V
V _F	forward voltage	I _F = 2 A; T _j = 25 °C		-	1.04	1.5	V
h _{FE}	DC current gain	$I_C = 1 \text{ mA}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see Figure 10		10	15	32	
		$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>		13	21	32	
		$I_C = 2 \text{ A}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see Figure 10		11	16	22	
		$I_C = 3 \text{ A}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see Figure 10		-	12.5	-	
Dynamic	characteristics						
t _{on}	turn-on time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω ; T_j 25 °C; resistive load; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	0.52	0.6	μs
t _s	storage time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω ; T_j = 25 °C; resistive load; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	2.7	3.3	μs
		$I_C = 2 \text{ A}$; $I_{Bon} = 0.4 \text{ A}$; $V_{BB} = -5 \text{ V}$; $L_B = 1 \mu \text{H}$; $T_j = 25 ^{\circ}\text{C}$; inductive load; see Figure 13; see Figure 14		-	1.2	1.4	μs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 μ H; T_j = 100 °C; inductive load; see Figure 13; see Figure 14		-	-	1.8	μs
t _f	fall time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω ; T_j = 25 °C; resistive load; see Figure 11; see Figure 12		-	0.3	0.35	μs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 μ H; T_j = 100 °C; inductive load; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	-	0.12	μs
		$I_C = 2$ A; $I_{Bon} = 0.4$ A; $V_{BB} = -5$ V; $L_B = 1$ μ H; T_j 25 °C; inductive load; see Figure 13; see Figure 14		-	0.03	0.06	μs

^[1] Measured with half-sine wave voltage (curve tracer)

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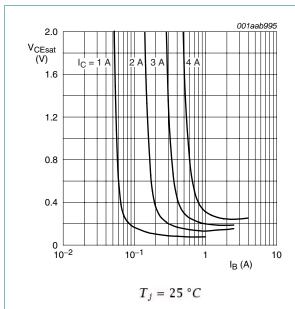


Fig 7. Collector-emitter saturation voltage as a function of base current; typical values

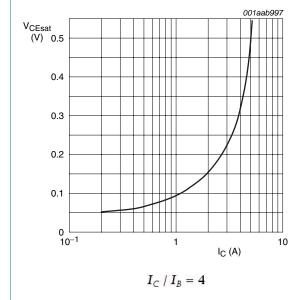


Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

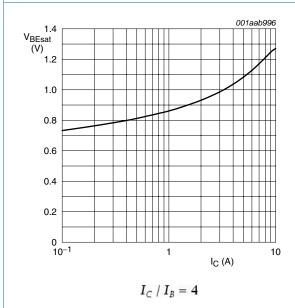


Fig 9. Base-emitter saturation voltage as a function of collector current; typical values

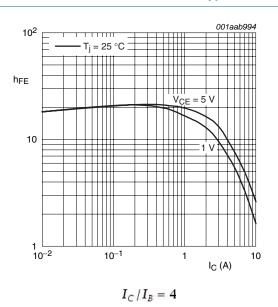
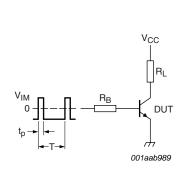


Fig 10. DC current gain as a function of collector current; typical values



$$V_{IM}=-6$$
 to $+8$ V ; $V_{CC}=250$ V ; $t_p=20$ μs ; $\boldsymbol{\delta}=\frac{t_p}{T}=0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 11. Test circuit for resistive load switching

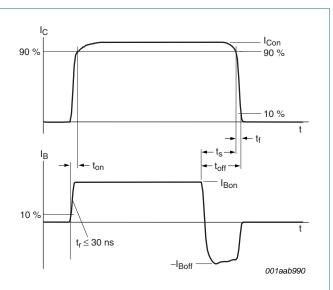
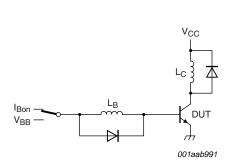


Fig 12. Switching times waveforms for resistive load



 $V_{CC} = 300 \text{ V}; V_{BB} = -5 \text{ V}; L_C = 200 \mu\text{H}; L_B = 1 \mu\text{H}$

Fig 13. Test circuit for inductive load switching

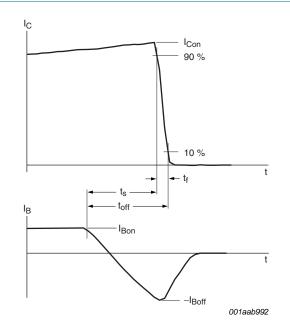


Fig 14. Switching times waveforms for inductive load

7. Package outline

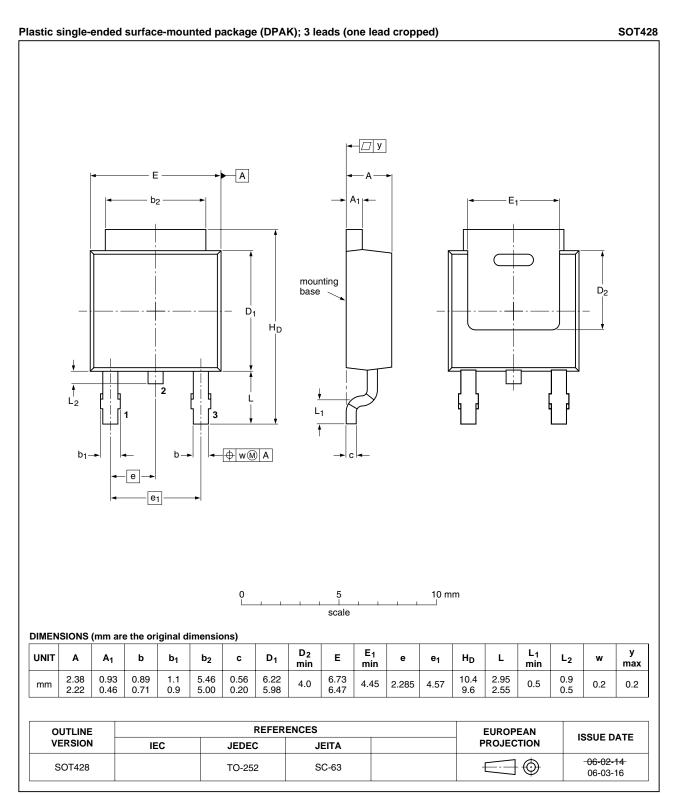


Fig 15. Package outline SOT428 (DPAK)



8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJD103AD v.3	20100803	Product data sheet	-	BUJD103AD v.2
Modifications:	 Various changes to 	content.		
BUJD103AD v.2	20091006	Product data sheet	-	BUJD103AD v.1

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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NXP Semiconductors

BUJD103AD

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